

Satoshi Shindo

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Inverse Resistance Change Cr ₂ Ge ₂ Te ₆ -Based PCRAM Enabling Ultralow-Energy Amorphization. ACS Applied Materials & Interfaces, 2018, 10, 2725-2734.	8.0	85
2	Contact resistance change memory using N-doped Cr ₂ Ge ₂ Te ₆ phase-change material showing non-bulk resistance change. Applied Physics Letters, 2018, 112, .	3.3	28
3	Cr-Triggered Local Structural Change in Cr ₂ Ge ₂ Te ₆ Phase Change Material. ACS Applied Materials & Interfaces, 2019, 11, 43320-43329.	8.0	26
4	Contact resistivity of amorphous and crystalline GeCu ₂ Te ₃ to W electrode for phase change random access memory. Materials Science in Semiconductor Processing, 2016, 47, 1-6.	4.0	24
5	Electronic Structure of Transition-Metal Based Cu ₂ GeTe ₃ Phase Change Material: Revealing the Key Role of Cu <i>d</i> Electrons. Chemistry of Materials, 2017, 29, 7440-7449.	6.7	24
6	Understanding the fast phase-change mechanism of tetrahedrally bonded Cu_2GeTe_3 : Comprehensive analyses of electronic structure and transport phenomena. Physical Review B, 2018, 97, .	3.2	11
7	The importance of contacts in Cu ₂ GeTe ₃ phase change memory devices. Journal of Applied Physics, 2020, 128, .	2.5	11
8	Molybdenum oxide-base phase change resistive switching material. Applied Physics Letters, 2017, 111, .	3.3	8
9	Chronological change of electrical resistance in GeCu ₂ Te ₃ amorphous film induced by surface oxidation. Journal Physics D: Applied Physics, 2014, 47, 475302.	2.8	7
10	Systematic materials design for phase-change memory with small density changes for high-endurance non-volatile memory applications. Applied Physics Express, 2019, 12, 051008.	2.4	7
11	XAFS Analysis of Crystal GeCu ₂ Te ₃ Phase Change Material. Zeitschrift Fur Physikalische Chemie, 2016, 230, 433-443.	2.8	4
12	Impact of contact resistance on memory window in phase-change random access memory (PCRAM). Journal of Computational Electronics, 2016, 15, 1570-1576.	2.5	3
13	Observation of ultrafast amorphization dynamics in GeCu ₂ Te ₃ thin films using echelon-based single-shot transient absorbance spectroscopy. Applied Physics Letters, 2021, 119, .	3.3	3
14	Effect of surface cleaning on contact resistivity of amorphous GeCu ₂ Te ₃ to a W electrode. MRS Advances, 2016, 1, 2731-2736.	0.9	2
15	Investigation of bias polarity dependence of set operation in GeCu ₂ Te ₃ phase change memory. Electronics Letters, 2018, 54, 350-351.	1.0	2
16	Implementation of pulse timing discriminator functionality into a GeSbTe/GeCuTe double layer structure. Optics Express, 2017, 25, 26825.	3.4	1
17	Electrical Contact Property of GeCu ₂ Te ₃ Phase Change Material to Electrode. ECS Meeting Abstracts, 2016, , .	0.0	0
18	(Invited) Ge-Cu-Te Phase Change Material for Pcram Application. ECS Meeting Abstracts, 2016, , .	0.0	0